What is claimed is:

1. A symmetric crossover structure of two lines formed of a lower conductor layer and a higher conductor layer above a substrate, the structure comprising:

a first line branched to a first route and a second route; and

a second line branched to a third route and a fourth route;

wherein the first route has a first segment to cross over the third route from the higher conductor layer and a second segment to cross over the fourth route from the lower conductor layer, the second route has a third segment to cross over the third route from the lower conductor layer and a fourth segment to cross over the fourth route from the higher conductor layer, the third route has a fifth segment to cross over the second route from the higher conductor layer and a sixth segment to cross over the first route from the lower conductor layer, and the fourth route has a seventh segment to cross over the second route from the lower conductor layer and an eighth segment to cross over the first route from the higher conductor layer.

2. The crossover structure of claim 1, wherein the first

and third segments are connected together, the second and forth segments are connected together, the fifth and seventh segments are connected together, and the sixth and eighth segments are connected together.

3. The crossover structure of claim 1, wherein the first and sixth segments cross over to each other, the second and eighth segments cross over to each other, the third and fifth segments cross over to each other, and the fourth and seventh segments cross over to each other.

4. The crossover structure of claim 1, wherein the first and second routes form a first parasitic capacitor, and the third and fourth routes form a second parasitic capacitor.

5. The crossover structure of claim 4, wherein the first and second parasitic capacitors are symmetric to the center of the crossover structure.